

SRT12 - SRT115

1.0 AMP. Schottky Barrier Rectifiers

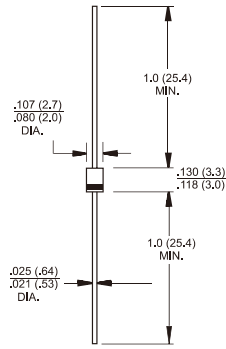
TS-1

Features

- ✦ Plastic material used carries Underwriters Laboratory Classification 94V-0
- ✦ Metal silicon junction, majority carrier conduction
- ✦ Low power loss, high efficiency
- ✦ High current capability, low forward voltage drop
- ✦ High surge capability
- ✦ Guard-ring for transient protection
- ✦ For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- ✦ High temperature soldering guaranteed: 260 °C /10seconds, 0.375" (9.5mm) lead length at 5 lbs. (2.3 kg) tension
- ✦ Green compound with suffix "G" on packing code & prefix "G" on datecode.

Mechanical Data

- ✦ Cases: Molded plastic body
- ✦ Terminals: Pure tin plated, lead free., solderable per MIL-STD-750, Method 2026
- ✦ Polarity: Color band denotes cathode
- ✦ Mounting position: Any
- ✦ Weight: 0.20 grams



Dimensions in inches and (millimeters)
Marking Diagram



SRT1X = Specific Device Code
G = Green Compound
Y = Year
M = Work Month

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%

Type Number	Symbol	SRT 12	SRT 13	SRT 14	SRT 15	SRT 16	SRT 19	SRT 110	SRT 115	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	20	30	40	50	60	90	100	150	V
Maximum RMS Voltage	V _{RMS}	14	21	28	35	42	63	70	105	V
Maximum DC Blocking Voltage	V _{DC}	20	30	40	50	60	90	100	150	V
Maximum Average Forward Rectified Current See Fig. 1	I _{F(AV)}	1.0								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	25								A
Maximum Instantaneous Forward Voltage @ 1.0A	V _F	0.55		0.70		0.80		0.90		V
Maximum D.C. Reverse Current at Rated DC Blocking Voltage (Note1)	I _R	0.5				0.1				mA
		10		5		-				mA
		-				2				mA
Typical Junction Capacitance (Note 2)	C _j	110		80		28				pF
Typical Thermal Resistance (Note3)	R _{θJA}	50								°C/W
Operating Junction Temperature Range	T _J	-65 to + 1 5				-65 to + 150				°C
Storage Temperature Range	T _{STG}	- 65 to + 150								°C

Notes: 1. Pulse Test with PW=300 usec, 1% Duty Cycle
2. Measured at 1.0 MHz and Applied V_R=4.0 Volts
3. Mount on Cu-Pad Size 5mm x 5mm on P.C.B.

Version: E10

RATINGS AND CHARACTERISTIC CURVES (SRT12 THRU SRT115)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

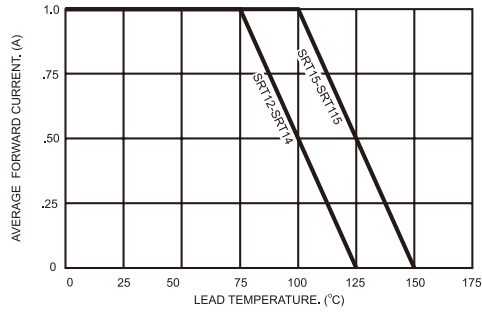


FIG.2- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

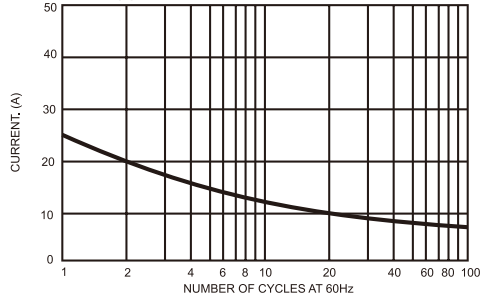


FIG.3- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

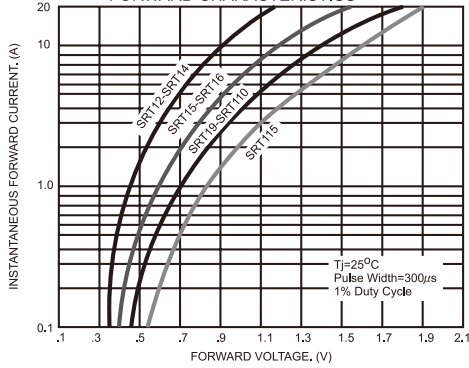


FIG.4- TYPICAL REVERSE CHARACTERISTICS

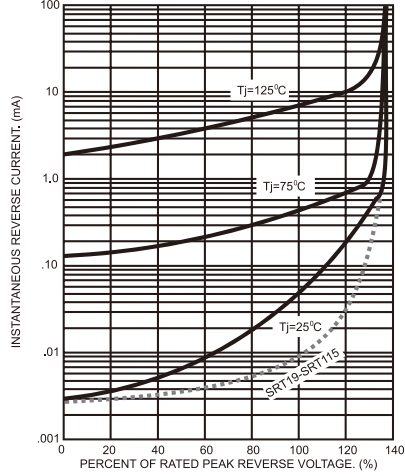


FIG.5- TYPICAL JUNCTION CAPACITANCE

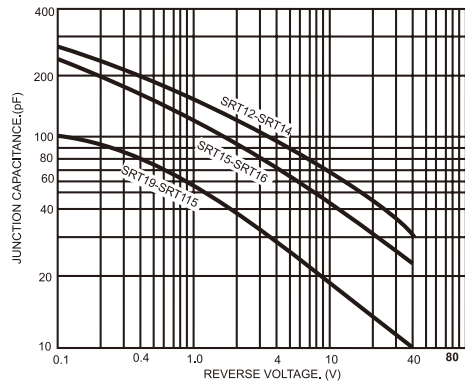


FIG.6- TYPICAL TRANSIENT THERMAL CHARACTERISTICS

